

MOSFET
OptiMOS™ 5 Power-Transistor, 80 V

Features

- N-channel, normal level
- Very low on-resistance R_DS(on)
- Superior thermal resistance
- Optimized design for double side cooling
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Table with 3 columns: Parameter, Value, Unit. Rows include V_DS (80 V), R_DS(on),max (1.57 mΩ), I_D (323 A), Q_oss (123 nC), and Q_G (106 nC).

Table with 4 columns: Type/Ordering Code, Package, Marking, Related Links. Row 1: IQD016N08NM5CGSC, PG-WHTFN-9, RA, -

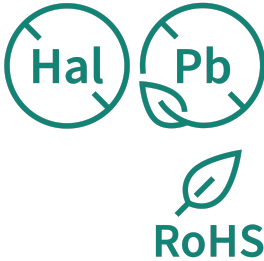
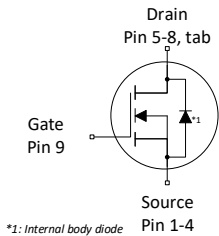
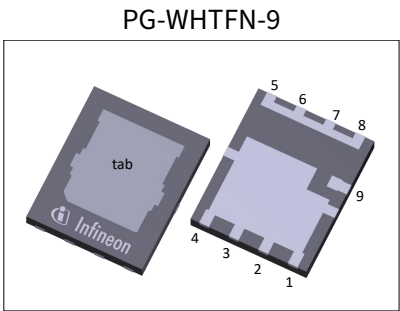




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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	323 229 188 31	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=6\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=50\text{ °C/W}$ ²⁾
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	1292	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ⁴⁾	E_{AS}	-	-	802	mJ	$I_D=50\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	333 3.0	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=50\text{ °C/W}$ ²⁾
Operating and storage temperature	T_j , T_{stg}	-55	-	175	°C	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for source connection. PCB is vertical in still air.

³⁾ See Diagram 3 for more detailed information

⁴⁾ See Diagram 13 for more detailed information

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	-	0.45	°C/W	-
Thermal resistance, junction - case, top	R_{thJC}	-	-	0.56	°C/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ⁵⁾	R_{thJA}	-	-	50	°C/W	-

⁵⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for source connection. PCB is vertical in still air.

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	80	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.2	3.0	3.8	V	$V_{DS}=V_{GS}$, $I_D=159\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=80\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=80\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.4 1.9	1.57 2.32	m Ω	$V_{GS}=10\text{ V}$, $I_D=50\text{ A}$ $V_{GS}=6\text{ V}$, $I_D=50\text{ A}$
Gate resistance	R_G	-	0.35	-	Ω	-
Transconductance	g_{fs}	-	140	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}$, $I_D=50\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Input capacitance ⁶⁾	C_{iss}	-	7100	9200	pF	$V_{GS}=0\text{ V}$, $V_{DS}=40\text{ V}$, $f=1\text{ MHz}$
Output capacitance ⁶⁾	C_{oss}	-	1200	1600	pF	$V_{GS}=0\text{ V}$, $V_{DS}=40\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance ⁶⁾	C_{rss}	-	56	98	pF	$V_{GS}=0\text{ V}$, $V_{DS}=40\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	15	-	ns	$V_{DD}=40\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	7	-	ns	$V_{DD}=40\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	29	-	ns	$V_{DD}=40\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	10	-	ns	$V_{DD}=40\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$

⁶⁾ Defined by design. Not subject to production test.

Table 6 Gate charge characteristics ⁷⁾

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	31	-	nC	$V_{DD}=40\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	21	-	nC	$V_{DD}=40\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge ⁸⁾	Q_{gd}	-	25	38	nC	$V_{DD}=40\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	35	-	nC	$V_{DD}=40\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total ⁸⁾	Q_g	-	106	133	nC	$V_{DD}=40\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	4.4	-	V	$V_{DD}=40\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	90	-	nC	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ⁸⁾	Q_{oss}	-	123	164	nC	$V_{DS}=40\text{ V}$, $V_{GS}=0\text{ V}$

⁷⁾ See "Gate charge waveforms" for parameter definition

⁸⁾ Defined by design. Not subject to production test.

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	256	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	1292	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.82	1.0	V	$V_{GS}=0\text{ V}$, $I_F=50\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery time ⁹⁾	t_{rr}	-	48	96	ns	$V_R=40\text{ V}$, $I_F=25\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge ⁹⁾	Q_{rr}	-	71	142	nC	$V_R=40\text{ V}$, $I_F=25\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery time ⁹⁾	t_{rr}	-	29	58	ns	$V_R=40\text{ V}$, $I_F=50\text{ A}$, $di_F/dt=1000\text{ A}/\mu\text{s}$
Reverse recovery charge ⁹⁾	Q_{rr}	-	331	662	nC	$V_R=40\text{ V}$, $I_F=50\text{ A}$, $di_F/dt=1000\text{ A}/\mu\text{s}$

⁹⁾ Defined by design. Not subject to production test.

4 Electrical characteristics diagrams

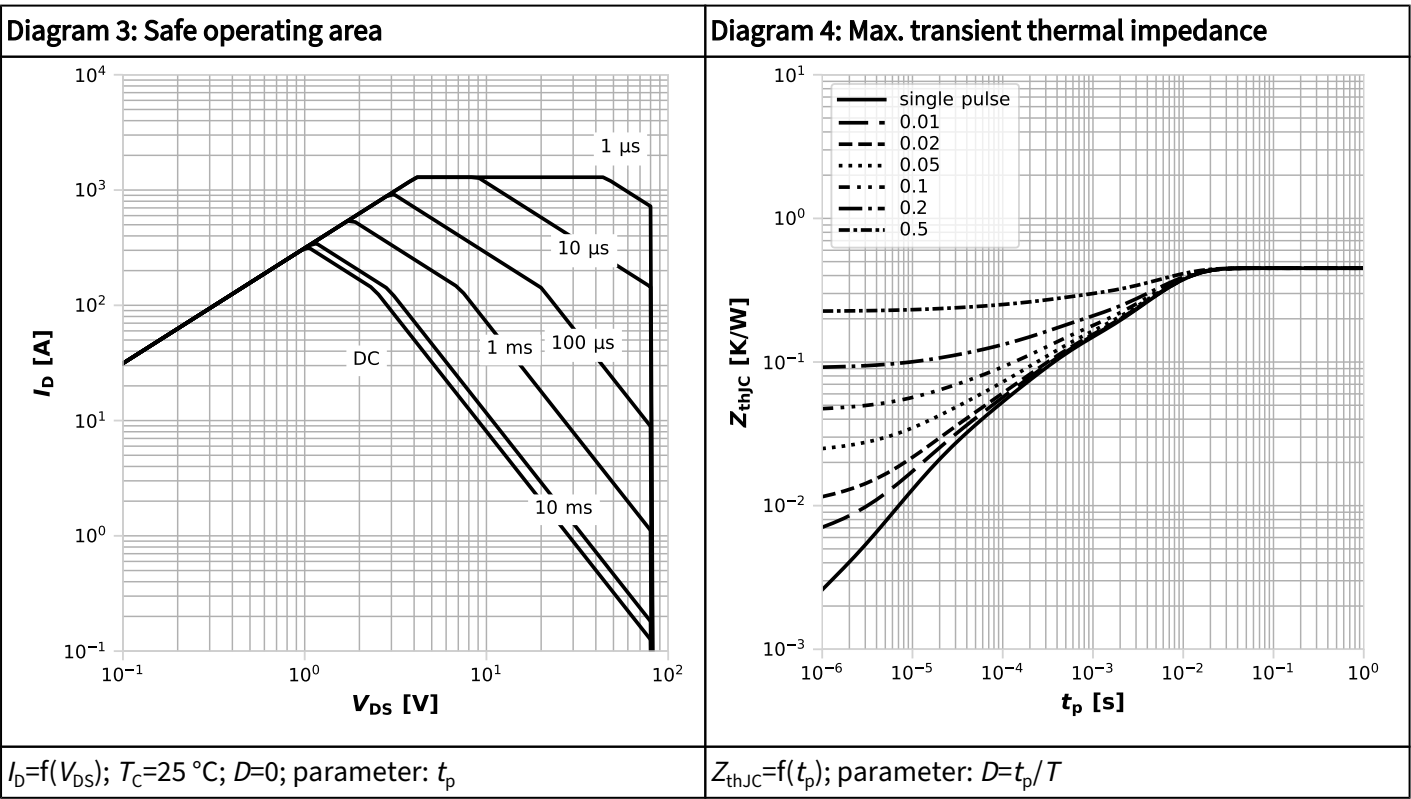
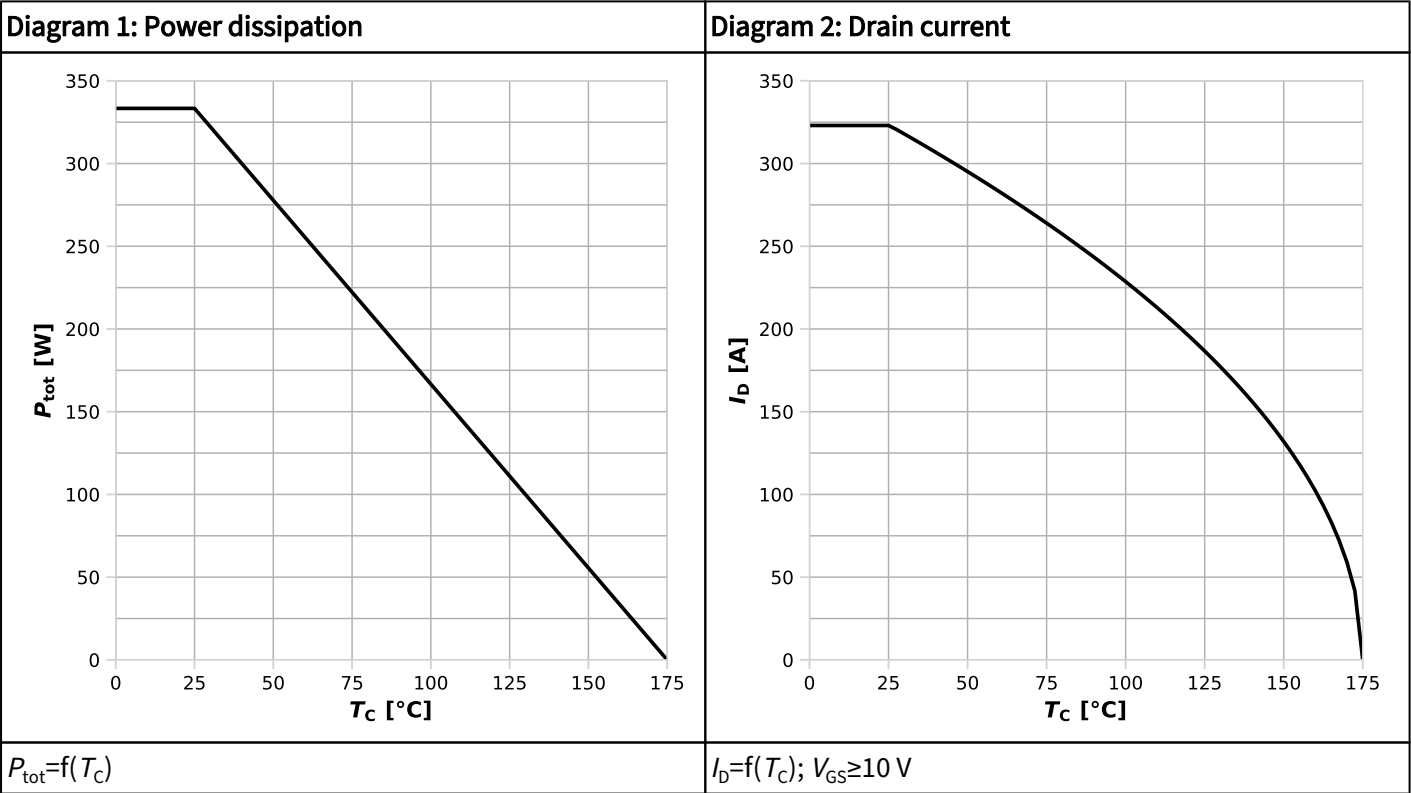
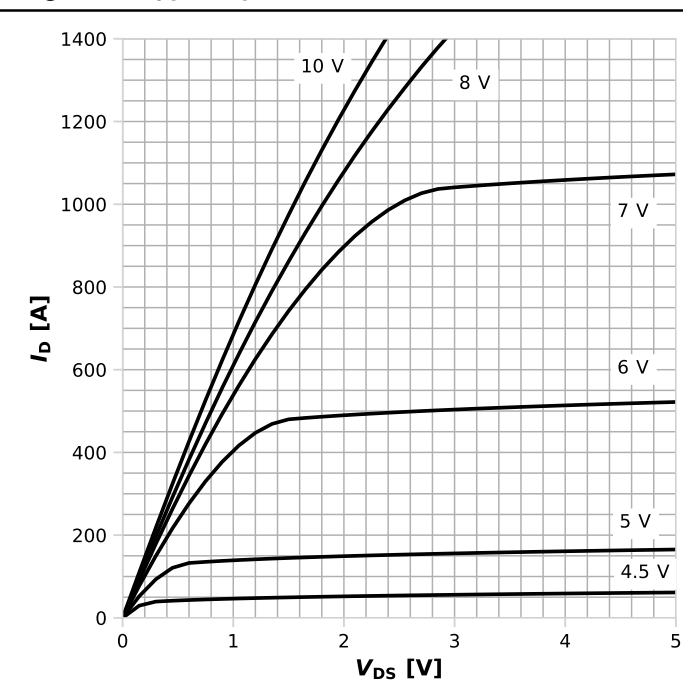
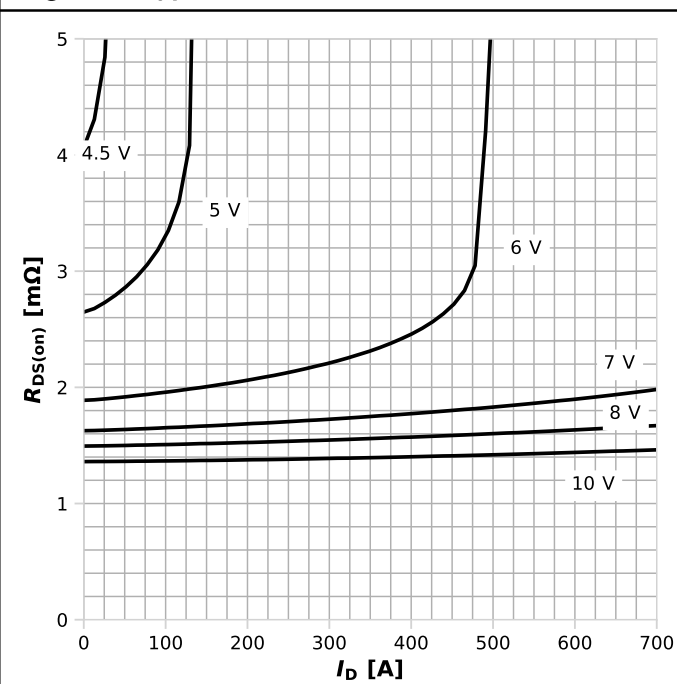


Diagram 5: Typ. output characteristics



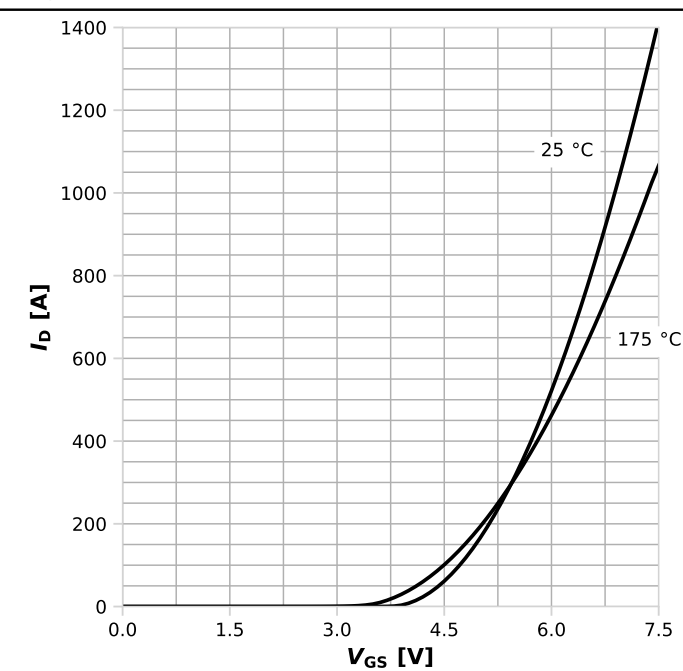
$I_D = f(V_{DS})$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



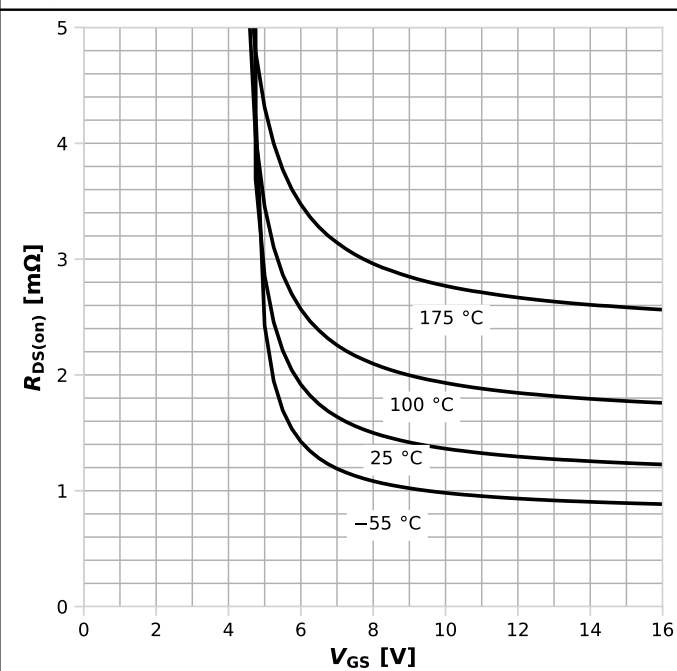
$R_{DS(on)} = f(I_D)$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



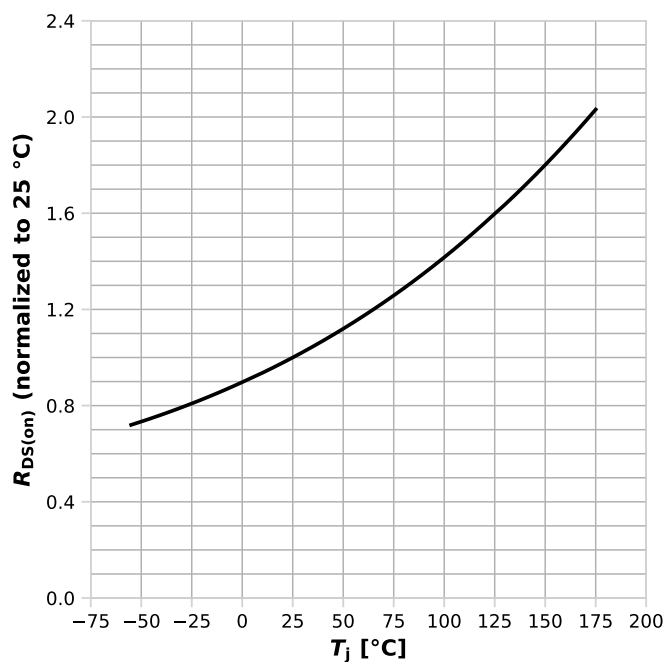
$I_D = f(V_{GS})$, $|V_{DS}| > 2|I_D|R_{DS(on)\max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



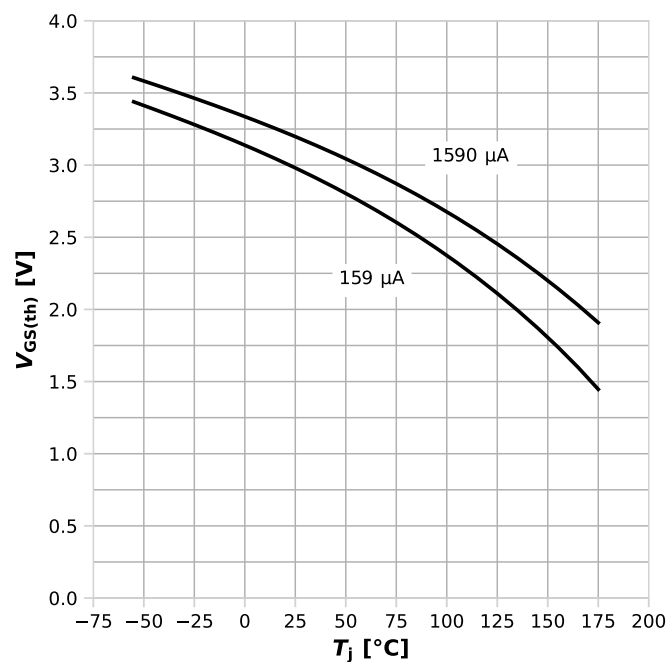
$R_{DS(on)} = f(V_{GS})$, $I_D = 50\text{ A}$; parameter: T_j

Diagram 9: Normalized drain-source on resistance



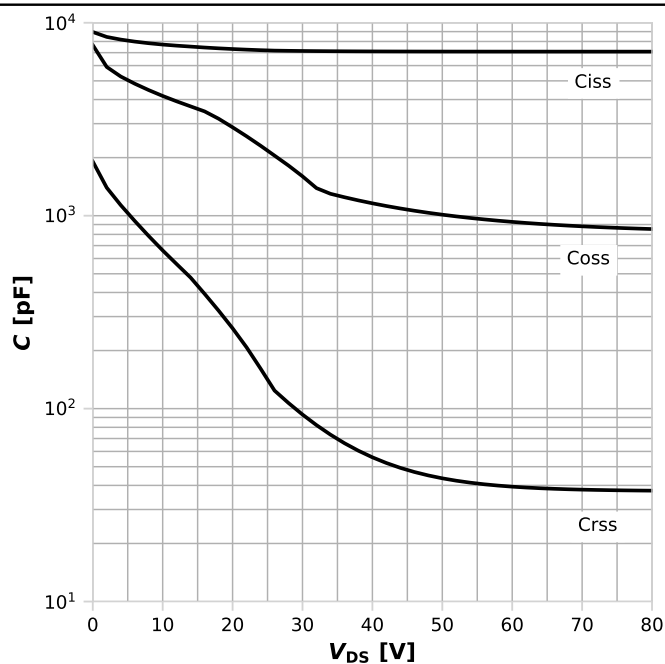
$$R_{DS(on)} = f(T_j), I_D = 50 \text{ A}, V_{GS} = 10 \text{ V}$$

Diagram 10: Typ. gate threshold voltage



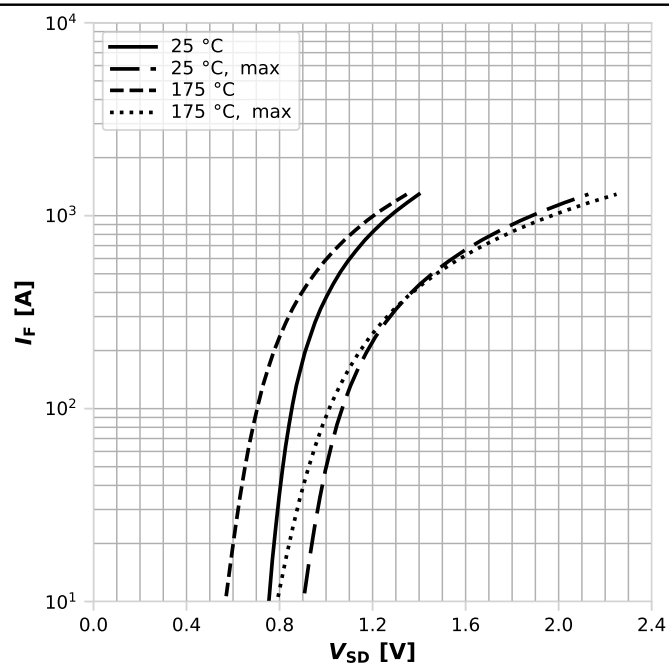
$$V_{GS(th)} = f(T_j), V_{GS} = V_{DS}; \text{ parameter: } I_D$$

Diagram 11: Typ. capacitances



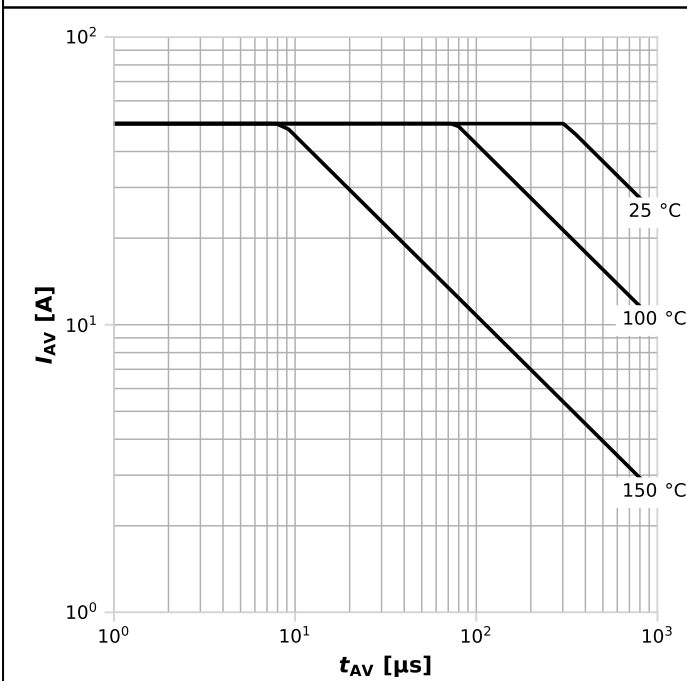
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 12: Forward characteristics of reverse diode



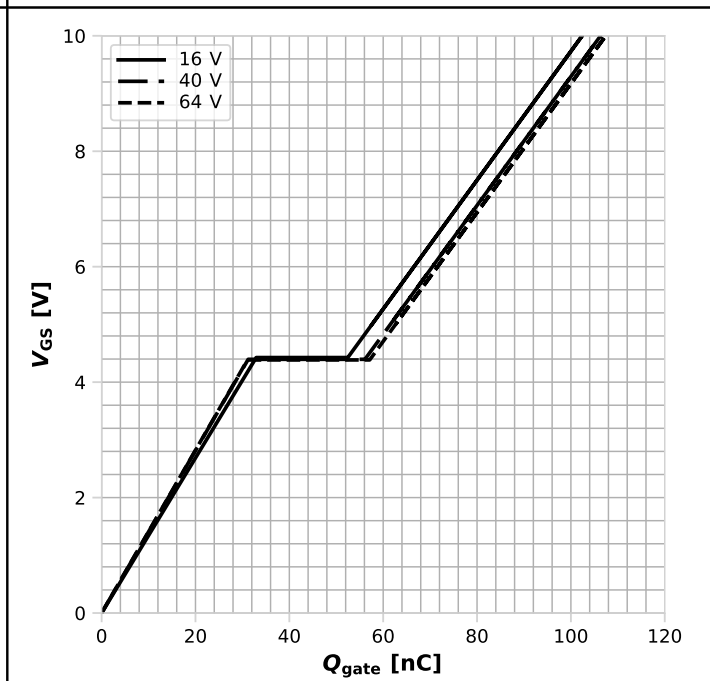
$$I_F = f(V_{SD}); \text{ parameter: } T_j$$

Diagram 13: Avalanche characteristics



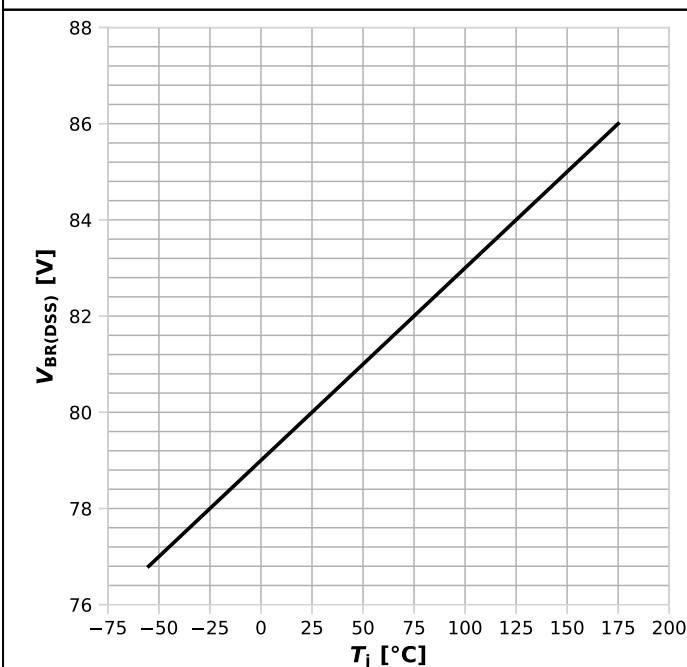
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



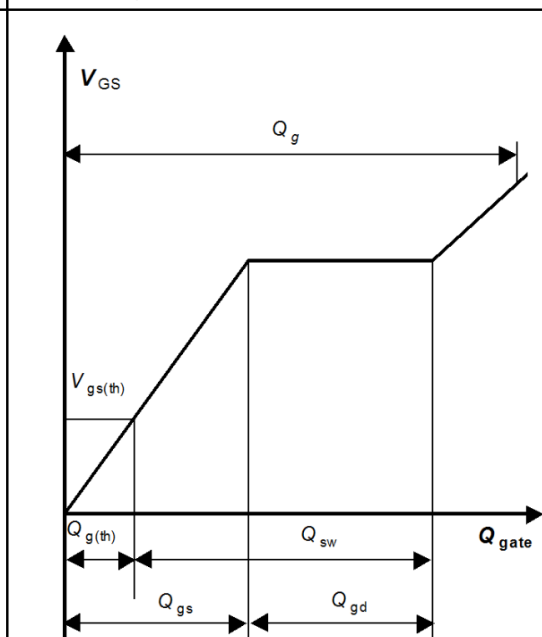
$V_{GS}=f(Q_{gate})$, $I_D=50\text{ A}$ pulsed, $T_j=25\text{ °C}$; parameter: V_{DD}

Diagram 15: Min. drain-source breakdown voltage



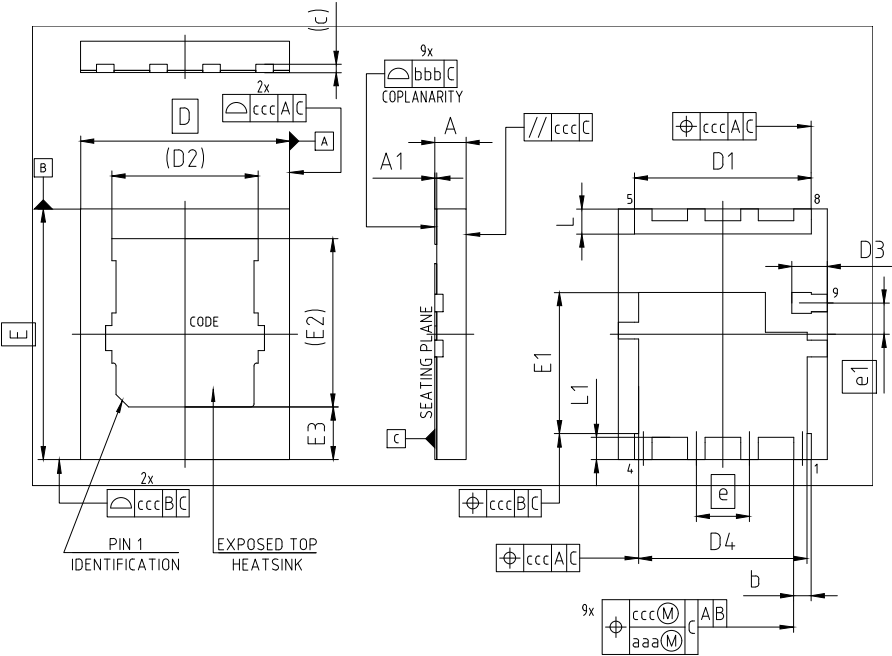
$V_{BR(DSS)}=f(T_j)$; $I_D=1\text{ mA}$

Gate charge waveforms



-

5 Package Outlines



PACKAGE - GROUP
NUMBER:

PG-WHTFN-9-U02

DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
A	0.55	0.75	e	1.27	
A1	0.00	0.05	e1	0.75	
b	0.32	0.52	L	0.50	0.70
c	0.20		L1	0.44	0.64
D	5.00		aaa	0.05	
D1	4.13	4.33	bbb	0.08	
D2	3.50		ccc	0.10	
D3	0.75	0.95			
D4	3.93	4.13			
E	6.00				
E1	3.28	3.48			
E2	4.03				
E3	1.16	1.36			

NOTE: DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS

Figure 1 Outline PG-WHTFN-9, dimensions in mm

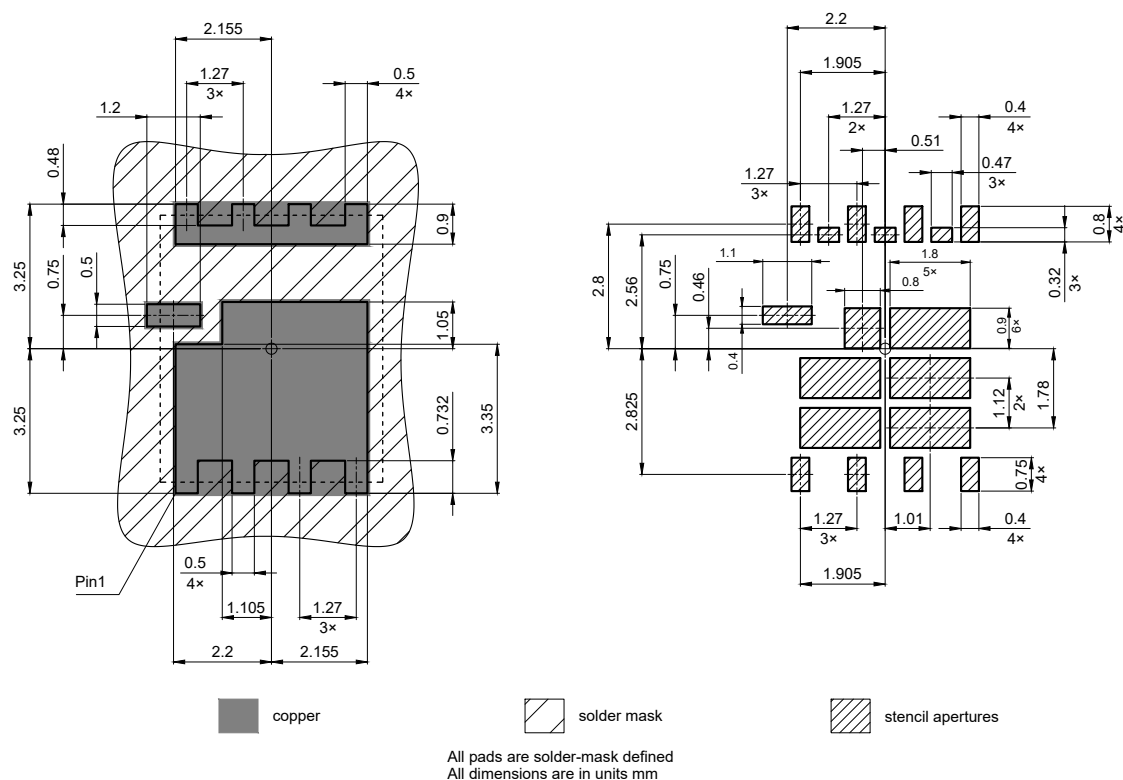


Figure 2 Footprint Drawing PG-WHTFN-9, dimensions in mm

Revision History

IQD016N08NM5CGSC

Revision 2024-10-12, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2024-06-14	Release of final
2.1	2024-10-12	Update package drawing and diagram circuit

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